NTB0101

Dual supply translating transceiver; auto direction sensing; 3-state

Rev. 2 — 5 May 2011

Product data sheet

1. General description

The NTB0101 is a 1-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features two 1-bit input-output ports (A and B), one output enable input (OE) and two supply pins ($V_{CC(A)}$ and $V_{CC(B)}$). $V_{CC(A)}$ can be supplied at any voltage between 1.2 V and 3.6 V and $V_{CC(B)}$ can be supplied at any voltage between 1.65 V and 5.5 V, making the device suitable for translating between any of the low voltage nodes (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V and 5.0 V).

Pins A and OE are referenced to $V_{CC(A)}$ and pin B is referenced to $V_{CC(B)}$. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range:
 - ◆ V_{CC(A)}: 1.2 V to 3.6 V and V_{CC(B)}: 1.65 V to 5.5 V
- I_{OFF} circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
 - ♦ HBM JESD22-A114E Class 2 exceeds 2500 V for A port
 - ◆ HBM JESD22-A114E Class 3B exceeds 15000 V for B port
 - ♦ MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1500 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
NTB0101GW	−40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
NTB0101GV	−40 °C to +125 °C	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457
NTB0101GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886
NTB0101GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891
NTB0101GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202

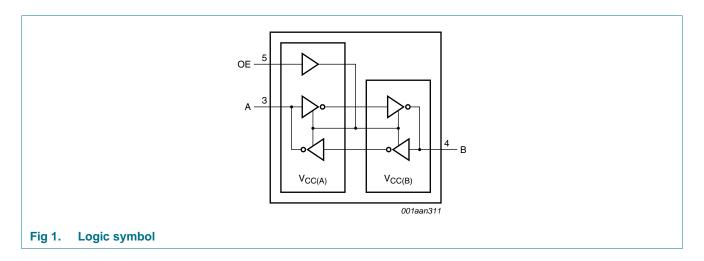
4. Marking

Table 2. Marking

rabio 21 Marking	
Type number	Marking code ^[1]
NTB0101GW	t1
NTB0101GV	t01
NTB0101GM	t1
NTB0101GF	t1
NTB0101GS	t1

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

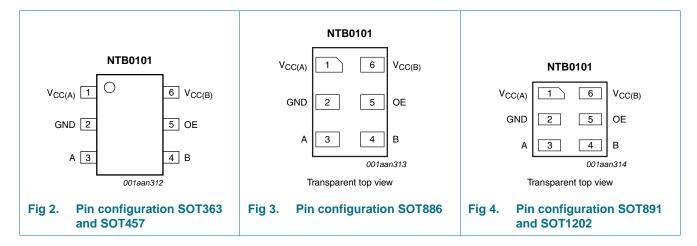
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
V _{CC(A)}	1	supply voltage A
GND	2	ground (0 V)
A	3	data input or output (referenced to V _{CC(A)})
В	4	data input or output (referenced to $V_{CC(B)}$)
OE	5	output enable input (active HIGH; referenced to $V_{\text{CC(A)}}$)
V _{CC(B)}	6	supply voltage B

7. Functional description

Table 4. Function table [1]

Supply voltage		Input	Input/output	
V _{CC(A)}	V _{CC(B)}	OE	A	В
1.2 V to V _{CC(B)}	1.65 V to 5.5 V	L	Z	Z
1.2 V to V _{CC(B)}	1.65 V to 5.5 V	Н	input or output	output or input
GND[2]	GND[2]	Χ	Z	Z

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

^[2] When either $V_{CC(A)}$ or $V_{CC(B)}$ is at GND level, the device goes into Power-down mode.

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

			•		
Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		-0.5	+6.5	V
$V_{CC(B)}$	supply voltage B		-0.5	+6.5	V
V_{I}	input voltage		<u>[1]</u> –0.5	+6.5	V
Vo	output voltage	Active mode	[1][2][3] -0.5	$V_{CCO} + 0.5$	V
		Power-down or 3-state mode	<u>[1]</u> –0.5	+6.5	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
lo	output current	$V_O = 0 V \text{ to } V_{CCO}$	[2] _	±50	mA
I _{CC}	supply current	I _{CC(A)} or I _{CC(B)}	-	100	mA
I_{GND}	ground current		-100	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[4]</u> _	250	mW

^[1] The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions[1][2]

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC(A)}$	supply voltage A		1.2	3.6	V
V _{CC(B)}	supply voltage B		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	Power-down or 3-state mode; $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$			
		A port	0	3.6	V
		B port	0	5.5	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	40	ns/V

^[1] The A and B sides of an unused I/O pair must be held in the same state, both at V_{CCI} or both at GND.

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^[2] V_{CCO} is the supply voltage associated with the output.

^[3] V_{CCO} + 0.5 V should not exceed 6.5 V.

^[4] For SC-88 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

^[2] $V_{CC(A)}$ must be less than or equal to $V_{CC(B)}$.

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10. Static characteristics

Table 7. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{OH}	HIGH-level output voltage	A port; $V_{CC(A)} = 1.2 \text{ V}$; $I_O = -20 \mu\text{A}$	-	1.1	-	V
V _{OL}	LOW-level output voltage	A port; $V_{CC(A)} = 1.2 \text{ V}$; $I_O = 20 \mu\text{A}$	-	0.09	-	V
II	input leakage current	OE input; $V_I = 0 \text{ V to } 3.6 \text{ V}; V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V}; V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	±1	μА
I _{OZ}	OFF-state output current	A or B port; V_O = 0 V to V_{CCO} ; $V_{CC(A)}$ = 1.2 V to 3.6 V; $V_{CC(B)}$ = 1.65 V to 5.5 V	[1] -	-	±1	μΑ
I _{OFF}	power-off leakage current	A port; V_1 or $V_O = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0$ V to 5.5 V	-	-	±1	μА
		B port; V_1 or $V_0 = 0$ V to 5.5 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0$ V to 3.6 V	-	-	±1	μА
I _{CC}	supply current	$V_I = 0 \text{ V or } V_{CCI}; I_O = 0 \text{ A}$	[2]			
		$I_{CC(A)}$; $V_{CC(A)} = 1.2 \text{ V}$; $V_{CC(B)} = 1.65 \text{ V}$ to 5.5 V	-	0.05	-	μΑ
		$I_{CC(B)}$; $V_{CC(A)} = 1.2 \text{ V}$; $V_{CC(B)} = 1.65 \text{ V}$ to 5.5 V	-	3.3	-	μΑ
		$I_{CC(A)} + I_{CC(B)}$; $V_{CC(A)} = 1.2 \text{ V}$; $V_{CC(B)} = 1.65 \text{ V}$ to 5.5 V	-	3.5	-	μΑ
C _I	input capacitance	OE input; $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V}; V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	1.0	-	pF
C _{I/O}	input/output	A port; $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V}; V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	4.0	-	pF
	capacitance	B port; V _{CC(A)} = 1.2 V to 3.6 V; V _{CC(B)} = 1.65 V to 5.5 V	-	7.5	-	pF

^[1] V_{CCO} is the supply voltage associated with the output.

Table 8. Typical supply current

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T_{amb} = 25 °C.

V _{CC(A)}	V _{CC(B)}								
	1.8	3 V	2.	2.5 V		3.3 V		5.0 V	
	I _{CC(A)}	I _{CC(B)}							
1.2 V	10	10	10	10	10	20	10	1050	nA
1.5 V	10	10	10	10	10	10	10	650	nA
1.8 V	10	10	10	10	10	10	10	350	nA
2.5 V	-	-	10	10	10	10	10	40	nA
3.3 V	-	-	-	-	10	10	10	10	nA

^[2] V_{CCI} is the supply voltage associated with the input.

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Table 9. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		–40 °C to	+85 °C	-40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
V_{IH}	HIGH-level	A or B port and OE input	<u>[1]</u>					'
	input voltage	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		0.65V _{CCI}	-	0.65V _{CCI}	-	V
V_{IL}	LOW-level	A or B port and OE input	[1]					
	input voltage	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	0.35V _{CCI}	-	0.35V _{CCI}	V
V_{OH}	HIGH-level	$I_{O} = -20 \mu A$	[2]					
output voltag	output voltage	A port; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V}$		$V_{CCO}-0.4$	-	$V_{CCO}-0.4$	-	V
		B port; $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		$V_{CCO}-0.4$	-	$V_{CCO}-0.4$	-	V
V_{OL}	LOW-level	I _O = 20 μA	[2]					
	output voltage	A port; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V}$		-	0.4	-	0.4	V
		B port; $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	0.4	-	0.4	V
I _I	input leakage current	OE input; $V_I = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	±2	-	±5	μА
I _{OZ}	OFF-state output current	A or B port; $V_O = 0 \text{ V or } V_{CCO}$; $V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V}$; $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	[2]	-	±2	-	±10	μА
I _{OFF}	power-off leakage	A port; V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC(A)} = 0$ V; $V_{CC(B)} = 0$ V to 5.5 V		-	±2	-	±10	μА
	current	B port; V_1 or $V_0 = 0$ V to 5.5 V; $V_{CC(B)} = 0$ V; $V_{CC(A)} = 0$ V to 3.6 V		-	±2	-	±10	μА

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Table 9. Static characteristics ...continued
At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		–40 °C t	o +85 °C	-40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
I _{CC}	supply current	$V_I = 0 \text{ V or } V_{CCI}; I_O = 0 \text{ A}$	<u>[1]</u>				'	
		I _{CC(A)}						
		OE = LOW; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	3	-	15	μΑ
		OE = HIGH; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	3	-	20	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$		-	2	-	15	5 μA
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 5.5 \text{ V}$ 2	-	-15	μΑ			
		$I_{CC(B)}$						
		OE = LOW; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	5	-	15	μΑ
		OE = HIGH; $V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	5	-	20	μΑ
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$		-	-2	-	-15	μΑ
		$V_{CC(A)} = 0 \text{ V}; V_{CC(B)} = 5.5 \text{ V}$		-	2	-	15	μΑ
		$I_{CC(A)} + I_{CC(B)}$						
		$V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	8	-	40	μА

^[1] V_{CCI} is the supply voltage associated with the input.

11. Dynamic characteristics

Table 10. Typical dynamic characteristics for temperature 25 °C[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for waveforms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions			V _C	C(B)		Unit
				1.8 V	2.5 V	3.3 V	5.0 V	
$V_{CC(A)} = 1$	1.2 V; T _{amb} = 25 °C							
t _{pd}	propagation delay	A to B		5.9	4.8	4.4	4.2	ns
		B to A		5.6	4.8	4.5	4.4	ns
t _{en}	enable time	OE to A, B		0.5	0.5	0.5	0.5	μS
t _{dis}	disable time	OE to A; no external load	[2]	6.9	6.9	6.9	6.9	ns
		OE to B; no external load	[2]	9.5	8.6	8.5	8.0	ns
		OE to A		81	69	83	68	ns
		OE to B		81	69	83	68	ns

^[2] V_{CCO} is the supply voltage associated with the output.

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Table 10. Typical dynamic characteristics for temperature 25 °C[1] ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 7</u>; for waveforms see <u>Figure 5</u> and <u>Figure 6</u>.

Symbol	Parameter	Conditions		V _{CC(B)}				
			1.8 V	2.5 V	3.3 V	5.0 V		
t _t	transition time	A port	4.0	4.0	4.1	4.1	ns	
		B port	2.6	2.0	1.7	1.4	ns	
t _W	pulse width	data inputs	15	13	13	13	ns	
f _{data}	data rate		70	80	80	80	Mbps	

 $[\]begin{array}{ll} [1] & t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}. \\ & t_{en} \text{ is the same as } t_{PZL} \text{ and } t_{PZH}. \\ & t_{dis} \text{ is the same as } t_{PLZ} \text{ and } t_{PHZ}. \end{array}$

Table 11. Dynamic characteristics for temperature range -40 °C to +85 °C[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions					Vcc	(B)				Unit
				1.8 V ±	0.15 V	2.5 V ±			± 0.3 V	5.0 V ±	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	1.5 V ± 0.1 V					'			1			1
t _{pd}	propagation	A to B		1.4	12.9	1.2	10.1	1.1	10.0	0.8	9.9	ns
	delay	B to A		0.9	14.2	0.7	12.0	0.4	11.7	0.3	13.7	ns
t _{en}	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	1.0	11.9	1.0	11.9	1.0	11.9	1.0	11.9	ns
		OE to B; no external load	[2]	1.0	16.9	1.0	15.2	1.0	14.1	1.0	13.8	ns
		OE to A		-	320	-	260	-	260	-	280	ns
		OE to B		-	200	-	200	-	200	-	200	ns
t _t	transition time	A port		0.9	5.1	0.9	5.1	0.9	5.1	0.9	5.1	ns
		B port		0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t _W	pulse width	data inputs		25	-	25	-	25	-	25	-	ns
f _{data}	data rate			-	40	-	40	-	40	-	40	Mbps
V _{CC(A)} =	1.8 V ± 0.15 V											
t _{pd}	propagation	A to B		1.6	11.0	1.4	7.7	1.3	6.8	1.2	6.5	ns
	delay	B to A		1.5	12.0	1.3	8.4	1.0	7.6	0.9	7.1	ns
t _{en}	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	1.0	11.0	1.0	11.0	1.0	11.0	1.0	11.0	ns
		OE to B; no external load	[2]	1.0	15.4	1.0	13.5	1.0	12.4	1.0	12.1	ns
		OE to A		-	260	-	230	-	230	-	230	ns
		OE to B		-	200	-	200	-	200	-	200	ns
t _t	transition	A port		8.0	4.1	8.0	4.1	8.0	4.1	8.0	4.1	ns
	time	B port		0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t _W	pulse width	data inputs		20	-	17	-	17	-	17	-	ns
f _{data}	data rate			-	49	-	60	-	60	-	60	Mbps

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t_t is the same as t_{THL} and t_{TLH}

^[2] Delay between OE going LOW and when the outputs are actually disabled.

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Table 11. Dynamic characteristics for temperature range –40 °C to +85 °C[1] ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions		V _{CC(B)}								Unit
				1.8 V ±	0.15 V	2.5 V ±	0.2 V	3.3 V	± 0.3 V	5.0 V	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	
V _{CC(A)} =	2.5 V ± 0.2 V											
t _{pd}	propagation	A to B		-	-	1.1	6.3	1.0	5.2	0.9	4.7	ns
	delay	B to A		-	-	1.2	6.6	1.1	5.1	0.9	4.4	ns
t _{en}	enable time	OE to A, B		-	-	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	-	-	1.0	9.2	1.0	9.2	1.0	9.2	ns
		OE to B; no external load	[2]	-	-	1.0	11.9	1.0	10.7	1.0	10.2	ns
		OE to A		-	-	-	200	-	200	-	200	ns
		OE to B		-	-	-	200	-	200	-	200	ns
t _t	transition time	A port		-	-	0.7	3.0	0.7	3.0	0.7	3.0	ns
		B port		-	-	0.7	3.2	0.5	2.5	0.4	2.7	ns
t_{W}	pulse width	data inputs		-	-	12	-	10	-	10	-	ns
f _{data}	data rate			-	-	-	85	-	100	-	100	Mbps
V _{CC(A)} =	3.3 V \pm 0.3 V											
t _{pd}	propagation	A to B		-	-	-	-	0.9	4.7	8.0	4.0	ns
	delay	B to A		-	-	-	-	1.0	4.9	0.9	3.8	ns
t _{en}	enable time	OE to A, B		-	-	-	-	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	-	-	-	-	1.0	9.2	1.0	9.2	ns
		OE to B; no external load	[2]	-	-	-	-	1.0	10.1	1.0	9.6	ns
		OE to A		-	-	-	-	-	260	-	260	ns
		OE to B		-	-	-	-	-	200	-	200	ns
t _t	transition	A port		-	-	-	-	0.7	2.5	0.7	2.5	ns
	time	B port		-	-	-	-	0.5	2.5	0.4	2.7	ns
t_{W}	pulse width	data inputs		-	-	-	-	10	-	10	-	ns
f _{data}	data rate			-	-	-	-	-	100	-	100	Mbps

^[1] t_{pd} is the same as t_{PLH} and t_{PHL} . t_{en} is the same as t_{PZL} and $t_{\text{PZH}}.$ $t_{\mbox{\scriptsize dis}}$ is the same as $t_{\mbox{\scriptsize PLZ}}$ and $t_{\mbox{\scriptsize PHZ}}.$ \boldsymbol{t}_{t} is the same as \boldsymbol{t}_{THL} and $\boldsymbol{t}_{TLH}.$

^[2] Delay between OE going LOW and when the outputs are actually disabled.

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Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C[1] Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 7</u>; for wave forms see <u>Figure 5</u> and <u>Figure 6</u>.

Symbol	Parameter	Conditions		V _{CC(B)}								Unit
				1.8 V ±	0.15 V	2.5 V ±	0.2 V	3.3 V	± 0.3 V	5.0 V	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	Ī
V _{CC(A)} =	1.5 V \pm 0.1 V											
t _{pd}	propagation	A to B		1.4	15.9	1.2	13.1	1.1	13.0	8.0	12.9	ns
	delay	B to A		0.9	17.2	0.7	15.0	0.4	14.7	0.3	16.7	ns
t _{en}	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	1.0	12.5	1.0	12.5	1.0	12.5	1.0	12.5	ns
		OE to B; no external load	[2]	1.0	18.1	1.0	16.2	1.0	14.9	1.0	14.6	ns
		OE to A		-	340	-	280	-	280	-	300	ns
		OE to B		-	220	-	220	-	220	-	220	ns
t _t	transition	A port		0.9	7.1	0.9	7.1	0.9	7.1	0.9	7.1	ns
	time	B port		0.9	6.5	0.6	5.2	0.5	4.8	0.4	4.7	ns
t _W	pulse width	data inputs		25	-	25	-	25	-	25	-	ns
f _{data}	data rate			-	40	-	40	-	40	-	40	Mbps
V _{CC(A)} =	1.8 V \pm 0.15 V											
t _{pd} propagation delay	A to B		1.6	14.0	1.4	10.7	1.3	9.8	1.2	9.5	ns	
	B to A		1.5	15.0	1.3	11.4	1.0	10.6	0.9	10.1	ns	
t _{en}	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS
t _{dis} d	disable time	OE to A; no external load	[2]	1.0	11.5	1.0	11.5	1.0	11.5	1.0	11.5	ns
		OE to B; no external load	[2]	1.0	16.5	1.0	14.5	1.0	13.3	1.0	12.7	ns
		OE to A		-	280	-	250	-	250	-	250	ns
		OE to B		-	220	-	220	-	220	-	220	ns
t _t	transition	A port		8.0	6.2	8.0	6.1	8.0	6.1	8.0	6.1	ns
	time	B port		0.9	5.8	0.6	5.2	0.5	4.8	0.4	4.7	ns
t _W	pulse width	data inputs		22	-	19	-	19	-	19	-	ns
f _{data}	data rate			-	45	-	55	-	55	-	55	Mbps
V _{CC(A)} =	2.5 V \pm 0.2 V											
t _{pd}	propagation	A to B		-	-	1.1	9.3	1.0	8.2	0.9	7.7	ns
	delay	B to A		-	-	1.2	9.6	1.1	8.1	0.9	7.4	ns
t _{en}	enable time	OE to A, B		-	-	-	1.0	-	1.0	-	1.0	μS
t _{dis}	disable time	OE to A; no external load	[2]	-	-	1.0	9.6	1.0	9.6	1.0	9.6	ns
		OE to B; no external load	[2]	-	-	1.0	12.6	1.0	11.4	1.0	10.8	ns
		OE to A		-	-	-	220	-	220	-	220	ns
		OE to B		-	-	-	220	-	220	-	220	ns
t _t	transition	A port		-	-	0.7	5.0	0.7	5.0	0.7	5.0	ns
	time	B port		-	-	0.7	4.6	0.5	4.8	0.4	4.7	ns
t _W	pulse width	data inputs;		-	-	14	-	13	-	10	-	ns
f _{data}	data rate			-	-	-	75	-	80	-	100	Mbps

Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C[1] ...continued Voltages are referenced to GND (ground = 0 V); for test circuit see <u>Figure 7</u>; for wave forms see <u>Figure 5</u> and <u>Figure 6</u>.

Symbol	Parameter	Conditions		V _{CC(B)}									
				1.8 V \pm 0.15 V 2.5 V		2.5 V	± 0.2 V	3.3 V \pm 0.3 V		5.0 V	± 0.5 V		
				Min	Max	Min	Max	Min	Max	Min	Max		
V _{CC(A)} =	3.3 V \pm 0.3 V			•	'				'	•	'		
t _{pd} propagation delay	A to B		-	-	-	-	0.9	7.7	0.8	7.0	ns		
	delay	B to A		-	-	-	-	1.0	7.9	0.9	6.8	ns	
t _{en}	enable time	OE to A, B		-	-	-	-	-	1.0	-	1.0	μS	
t _{dis}	disable time	OE to A; no external load	[2]	-	-	-	-	1.0	9.5	1.0	9.5	ns	
		OE to B; no external load	[2]	-	-	-	-	1.0	10.7	1.0	9.6	ns	
		OE to A		-	-	-	-	-	280	-	280	ns	
		OE to B		-	-	-	-	-	220	-	220	ns	
t _t	transition	A port		-	-	-	-	0.7	4.5	0.7	4.5	ns	
time	time	B port		-	-	-	-	0.5	4.1	0.4	4.7	ns	
t_{W}	pulse width	data inputs		-	-	-	-	10	-	10	-	ns	
f _{data}	data rate			-	-	-	-	-	100	-	100	Mbps	

 $[\]begin{array}{ll} [1] & t_{pd} \text{ is the same as } t_{PLH} \text{ and } t_{PHL}. \\ & t_{en} \text{ is the same as } t_{PZL} \text{ and } t_{PZH}. \\ & t_{dis} \text{ is the same as } t_{PLZ} \text{ and } t_{PHZ}. \\ & t_{t} \text{ is the same as } t_{THL} \text{ and } t_{TLH}. \end{array}$

^[2] Delay between OE going LOW and when the outputs are actually disabled.

Dual supply translating transceiver; auto direction sensing; 3-state

Table 13. Typical power dissipation capacitance

Voltages are referenced to GND (ground = 0 V).[1][2]

Symbol	Parameter	Conditions	V _{CC(A)}							
			1.2 V	1.2 V	1.5 V	1.8 V	2.5 V	2.5 V	3.3 V	
			V _{CC(B)}							
			1.8 V	5.0 V	1.8 V	1.8 V	2.5 V	5.0 V	3.3 V to 5.0 V	
$T_{amb} = 2$	5 °C									
, 5	power dissipation capacitance	outputs enabled; $OE = V_{CC(A)}$								
		A port: (direction A to B)	5	5	5	5	5	5	5	pF
		A port: (direction B to A)	8	8	8	8	8	8	8	pF
		B port: (direction A to B)	18	18	18	18	18	18	18	pF
		B port: (direction B to A)	13	16	12	12	12	12	13	pF
		outputs disabled; OE = GND								
		A port: (direction A to B)	0.12	0.12	0.04	0.05	0.08	0.08	0.07	pF
		A port: (direction B to A)	0.01	0.01	0.01	0.01	0.01	0.01	0.01	pF
		B port: (direction A to B)	0.01	0.01	0.01	0.01	0.01	0.01	0.01	pF
		B port: (direction B to A)	0.07	0.09	0.07	0.07	0.05	0.09	0.09	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

fo = output frequency in MHz;

C_L = load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

[2] f_i = 10 MHz; V_I = GND to V_{CC} ; t_f = t_f = 1 ns; C_L = 0 pF; R_L = ∞ Ω .

12. Waveforms

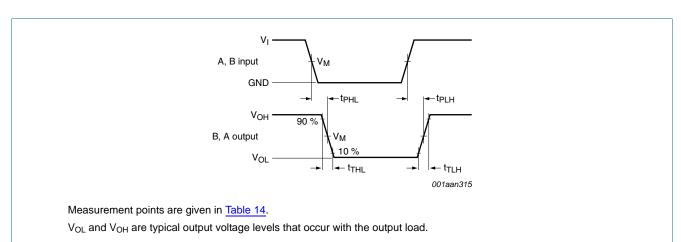


Fig 5. Data input (A, B) to data output (B, A) propagation delay times

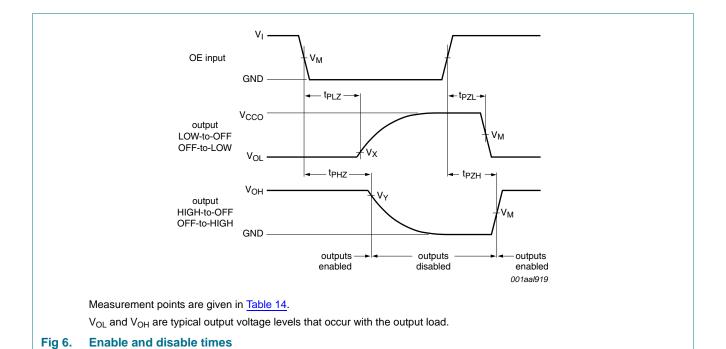
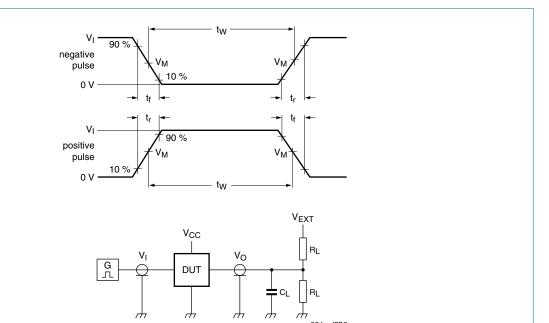


Table 14. Measurement points[1]

Supply voltage	Input	Output		
V _{CCO}	V _M	V _M	V _X	V _Y
1.2 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	$V_{OH} - 0.1 V$
1.5 V \pm 0.1 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.1 V	V _{OH} – 0.1 V
1.8 V \pm 0.15 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
$2.5~\textrm{V} \pm 0.2~\textrm{V}$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.15 V	V _{OH} – 0.15 V
3.3 V \pm 0.3 V	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$
$5.0~\textrm{V} \pm 0.5~\textrm{V}$	0.5V _{CCI}	0.5V _{CCO}	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$

 $^{[1] \}quad V_{CCI} \ is \ the \ supply \ voltage \ associated \ with \ the \ input \ and \ V_{CCO} \ is \ the \ supply \ voltage \ associated \ with \ the \ output.$

Dual supply translating transceiver; auto direction sensing; 3-state



Test data is given in Table 15.

All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz; Z_0 = 50 Ω ; $dV/dt \geq$ 1.0 V/ns.

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Test circuit for measuring switching times

Table 15. Test data

Supply voltage		Input		Load		V _{EXT}			
V _{CC(A)}	V _{CC(B)}	۷ _ا [1]	Δ t/ Δ V	CL	R _L [2]	t _{PLH} , t _{PHL}	t_{PZH}, t_{PHZ}	t _{PZL} , t _{PLZ} [3]	
1.2 V to 3.6 V	1.65 V to 5.5 V	V_{CCI}	\leq 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V _{CCO}	

^[1] V_{CCI} is the supply voltage associated with the input.

[3] V_{CCO} is the supply voltage associated with the output.

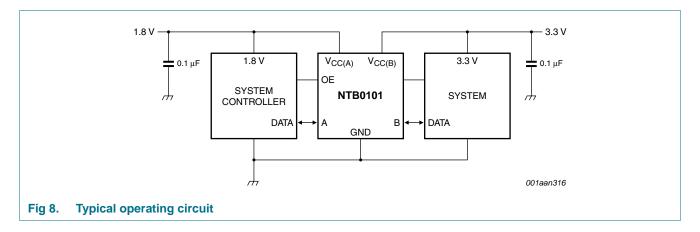
^[2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements, $R_L = 1 \text{ M}\Omega$; for measuring enable and disable times, $R_L = 50 \text{ k}\Omega$.

Dual supply translating transceiver; auto direction sensing; 3-state

13. Application information

13.1 Applications

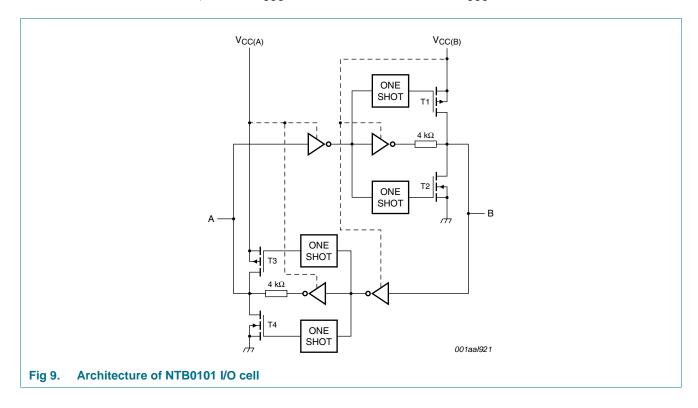
Voltage level-translation applications. The NTB0101 can be used to interface between devices or systems operating at different supply voltages. See <u>Figure 8</u> for a typical operating circuit using the NTB0101.



Dual supply translating transceiver; auto direction sensing; 3-state

13.2 Architecture

The architecture of the NTB0101 is shown in Figure 9. The device does not require an extra input signal to control the direction of data flow from A to B or from B to A. In a static state, the output drivers of the NTB0101 can maintain a defined output level, but the output architecture is designed to be weak, so that they can be overdriven by an external driver when data on the bus starts flowing in the opposite direction. The output of one-shot circuits detect rising or falling edges on the A or B ports. During a rising edge, the one-shot circuits turn on the PMOS transistors (T1, T3) for a short duration, accelerating the LOW-to-HIGH transition. Similarly, during a falling edge, the one-shot circuits turn on the NMOS transistors (T2, T4) for a short duration, accelerating the HIGH-to-LOW transition. During output transitions the typical output impedance is 70 Ω at $V_{\rm CCO}$ = 1.2 V to 1.8 V, 50 Ω at $V_{\rm CCO}$ = 1.8 V to 3.3 V and 40 Ω at $V_{\rm CCO}$ = 3.3 V to 5.0 V.

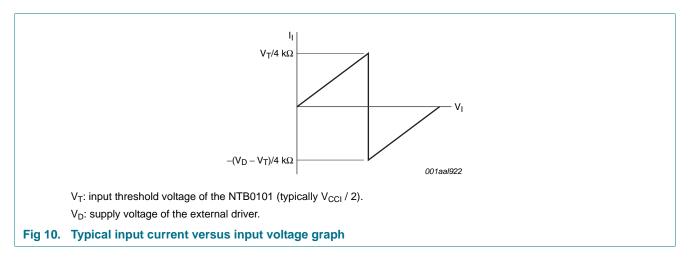


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Dual supply translating transceiver; auto direction sensing; 3-state

13.3 Input driver requirements

For correct operation, the device driving the data I/Os of the NTB0101 must have a minimum drive capability of ± 2 mA See Figure 10 for a plot of typical input current versus input voltage.



13.4 Power-up

During operation $V_{CC(A)}$ must never be higher than $V_{CC(B)}$, however during power-up $V_{CC(A)} \ge V_{CC(B)}$ does not damage the device, so either power supply can be ramped up first. There is no special power-up sequencing required. The NTB0101 includes circuitry that disables all output ports when either $V_{CC(A)}$ or $V_{CC(B)}$ is switched off.

13.5 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time (t_{dis} with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time (t_{en}) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND through a pull-down resistor, the minimum value of the resistor is determined by the current-sourcing capability of the driver.

13.6 Pull-up or pull-down resistors on I/O lines

As mentioned previously the NTB0101 is designed with low static drive strength to drive capacitive loads of up to 70 pF. To avoid output contention issues, any pull-up or pull-down resistors used must be above 50 k Ω . For this reason the NTB0101 is not recommended for use in open drain driver applications such as 1-Wire or I²C-bus. For these applications, the NTS0101 level translator is recommended.

Dual supply translating transceiver; auto direction sensing; 3-state

14. Package outline

Plastic surface-mounted package; 6 leads

SOT363

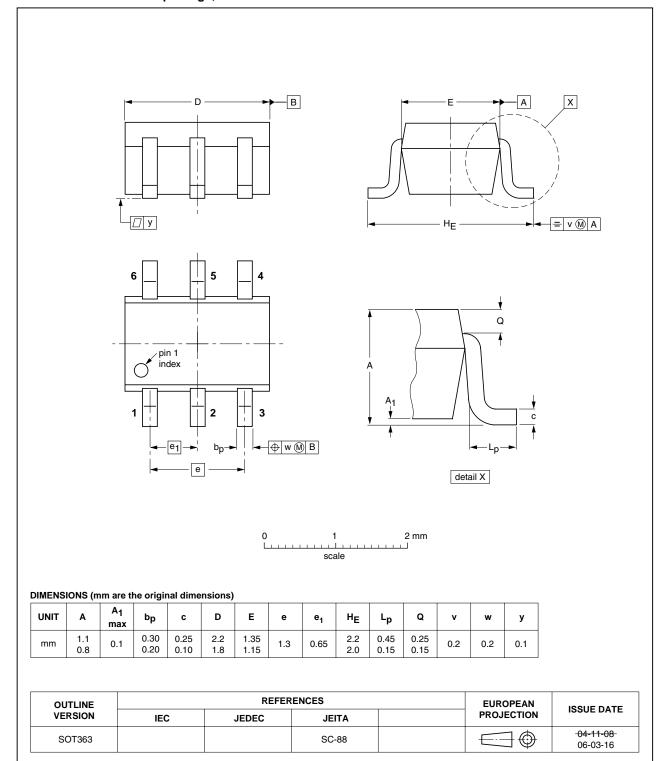


Fig 11. Package outline SOT363 (SC-88)

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Plastic surface-mounted package (TSOP6); 6 leads

SOT457

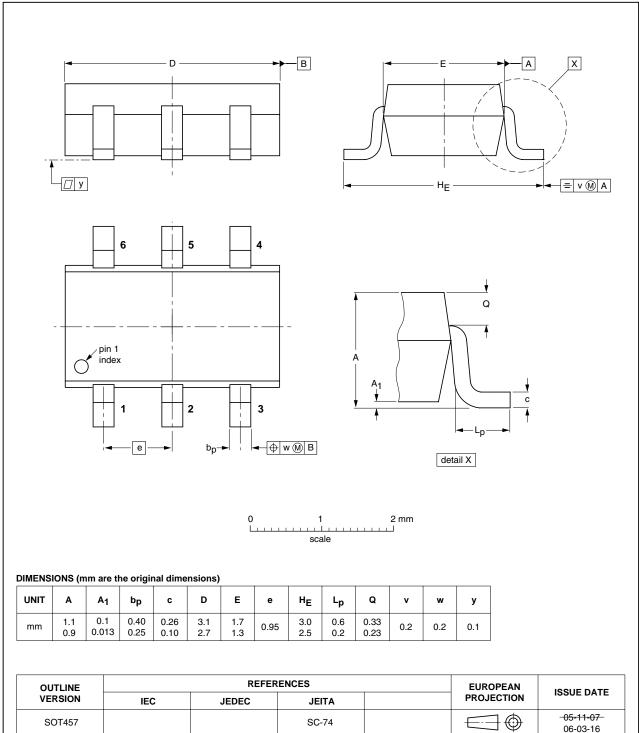


Fig 12. Package outline SOT457 (TSOP6)

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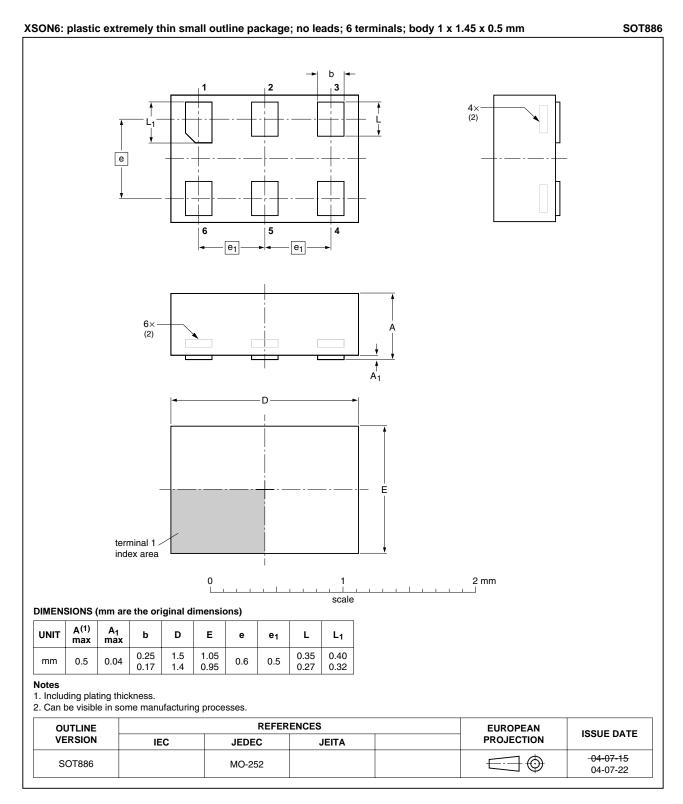


Fig 13. Package outline SOT886 (XSON6)

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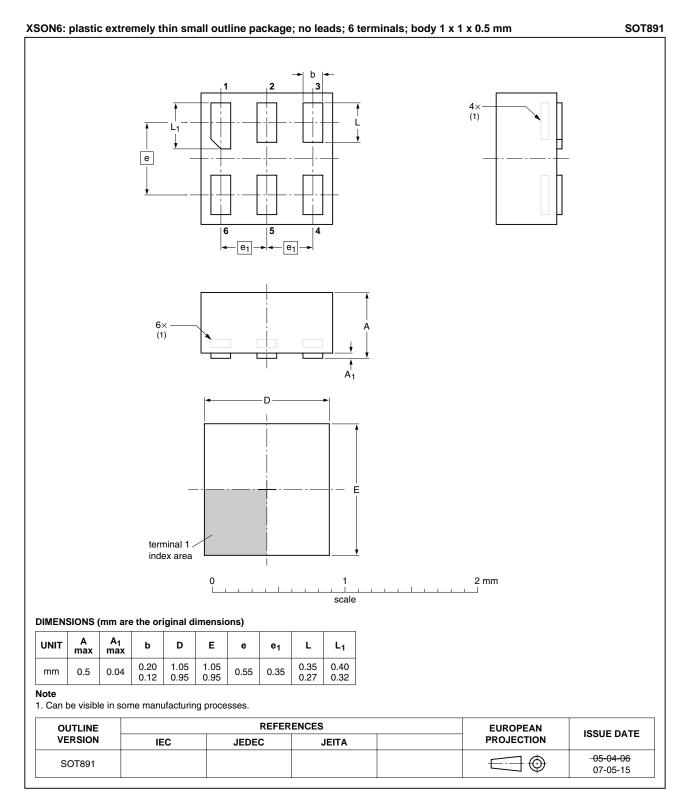


Fig 14. Package outline SOT891 (XSON6)

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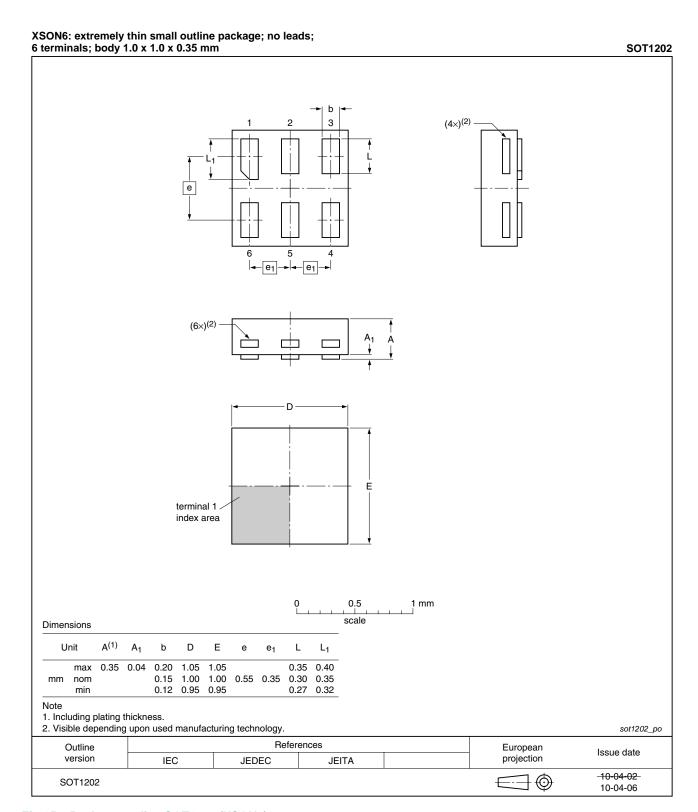


Fig 15. Package outline SOT1202 (XSON6)

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Dual supply translating transceiver; auto direction sensing; 3-state

15. Abbreviations

Table 16. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
NMOS	N-type Metal Oxide Semiconductor
PMOS	P-type Metal Oxide Semiconductor
PRR	Pulse Repetition Rate

16. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NTB0101 v.2	20110505	Product data sheet	-	NTB0101 v.1
Modifications:	 Added <u>Tab</u> 	le 7: total supply current (typ	ical).	
NTB0101 v.1	20101230	Product data sheet	-	-

Dual supply translating transceiver; auto direction sensing; 3-state

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17.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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